

PowerMOS transistor

BUK457-500A
BUK457-500B

T-39-13

GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in a plastic envelope.

The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BUK457	-500A	-500B	
V_{DS}	Drain-source voltage	500	500	V
I_D	Drain current (DC)	10	9	A
P_{tot}	Total power dissipation	150	150	W
$R_{DS(ON)}$	Drain-source on-state resistance	0.6	0.8	Ω

MECHANICAL DATA

Dimensions in mm

Net Mass: 2g

Pinning:

1 = Gate

2 = Drain

3 = Source

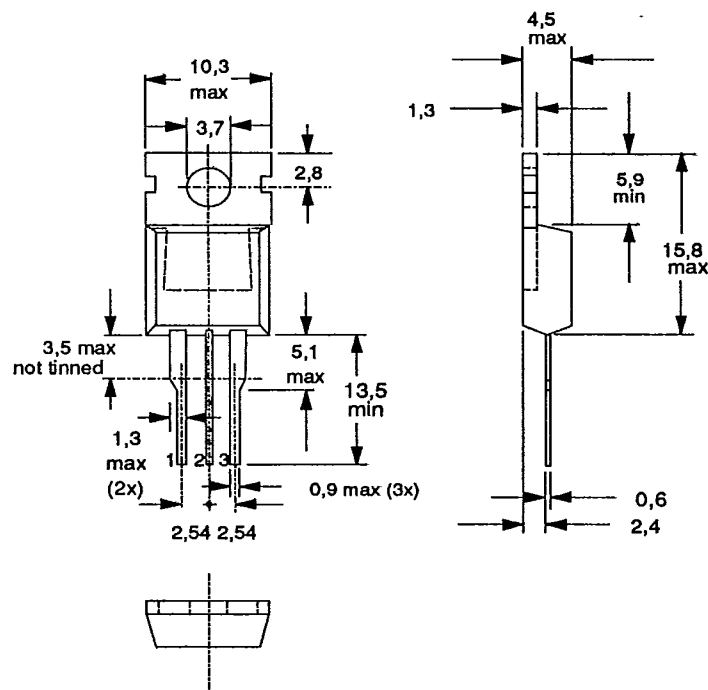
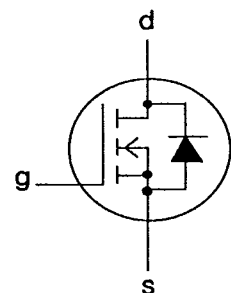


Fig.1 TO220AB; drain connected to mounting base.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Accessories supplied on request; refer to Mounting instructions for TO220 envelopes.

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	500	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	500	V
$\pm V_{GS}$	Gate-source voltage	-	-	30	V
I_D	Drain current (DC)	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	-500A 10	A
I_D	Drain current (DC)	$T_{mb} = 100 \text{ }^\circ\text{C}$	-	6.3	A
I_{DM}	Drain current (pulse peak value)	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	40	A
P_{tot}	Total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	150	W
T_{stg}	Storage temperature	-	-55	150	$^\circ\text{C}$
T_j	Junction Temperature	-	-	150	$^\circ\text{C}$

THERMAL RESISTANCES

From junction to mounting base	$R_{th\ j-mb} = 0.83 \text{ K/W}$
From junction to ambient	$R_{th\ j-a} = 60 \text{ K/W}$

STATIC CHARACTERISTICS

 $T_{mb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.25 \text{ mA}$	500	-	-	V
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1 \text{ mA}$	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 500 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	20	μA
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 500 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 30 \text{ V}; V_{DS} = 0 \text{ V}$	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 6.5 \text{ A}$	-	0.55	0.6	Ω
		BUK457-500A	-	0.7	0.8	Ω
		BUK457-500B	-			

DYNAMIC CHARACTERISTICS

 $T_{mb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	$V_{DS} = 25 \text{ V}; I_D = 6.5 \text{ A}$	5.0	8.0	-	S
C_{iss}	Input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}$	-	1500	1800	pF
C_{oss}	Output capacitance		-	170	270	pF
C_{rss}	Feedback capacitance		-	70	120	pF
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 30 \text{ V}; I_D = 2.8 \text{ A};$	-	20	40	ns
t_r	Turn-on rise time	$V_{GS} = 10 \text{ V}; R_{GS} = 50 \text{ }\Omega;$	-	60	90	ns
$t_{d\ off}$	Turn-off delay time	$R_{gen} = 50 \text{ }\Omega$	-	200	250	ns
t_f	Turn-off fall time		-	75	90	ns
L_d	Internal drain inductance	Measured from contact screw on tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

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REVERSE DIODE RATINGS AND CHARACTERISTICS

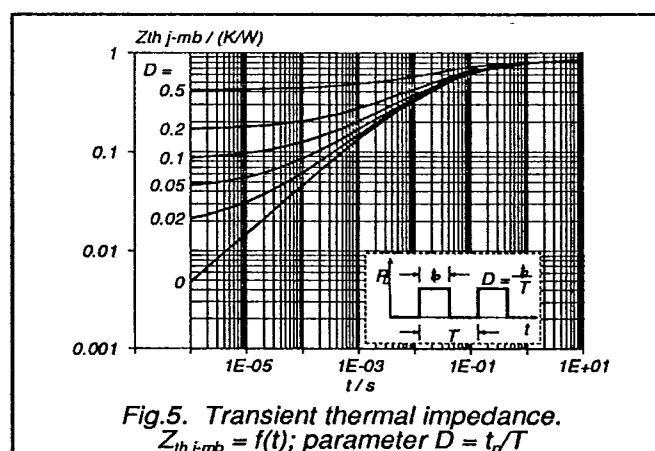
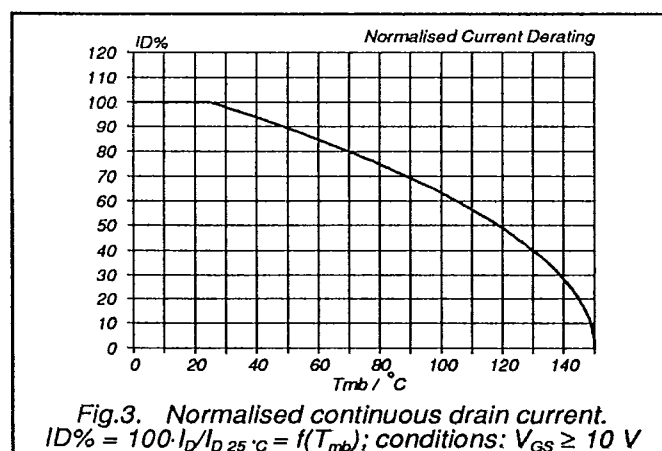
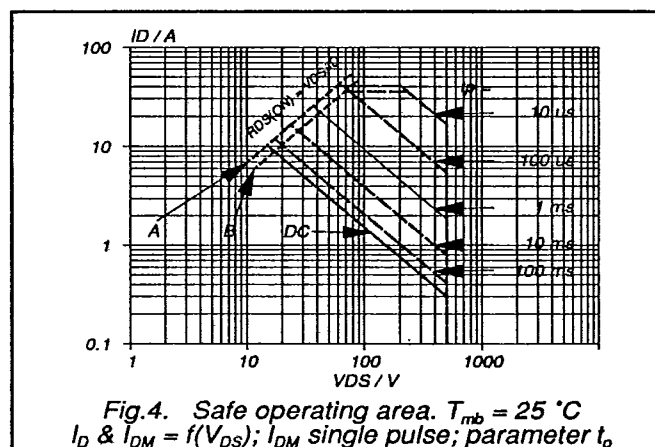
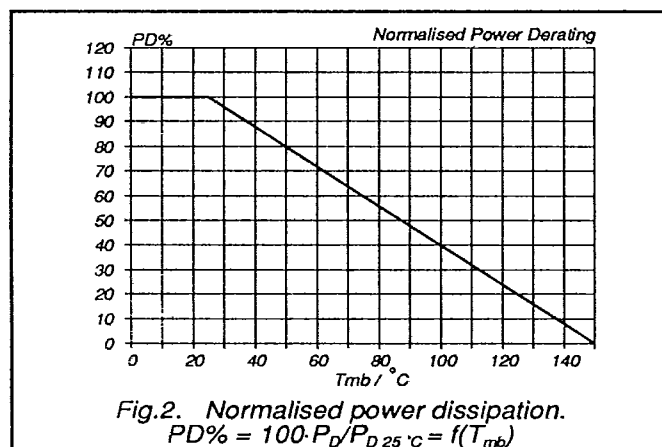
 $T_{mb} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	10	A
I_{DRM}	Pulsed reverse drain current	-	-	-	40	A
V_{SD}	Diode forward voltage	$I_F = 10\text{ A}; V_{GS} = 0\text{ V}$	-	1.1	1.4	V
t_{rr}	Reverse recovery time	$I_F = 10\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_R = 100\text{ V}$	-	500	-	ns
Q_{rr}	Reverse recovery charge	$I_F = 10\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_R = 100\text{ V}$	-	6.0	-	μC

AVALANCHE RATING

 $T_{mb} = 25^\circ\text{C}$ unless otherwise specified

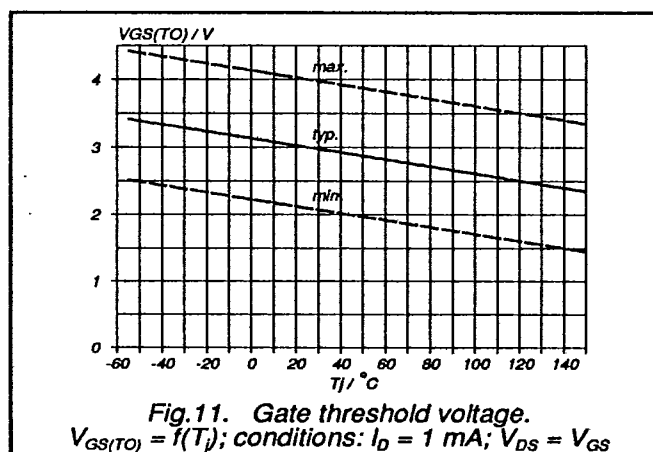
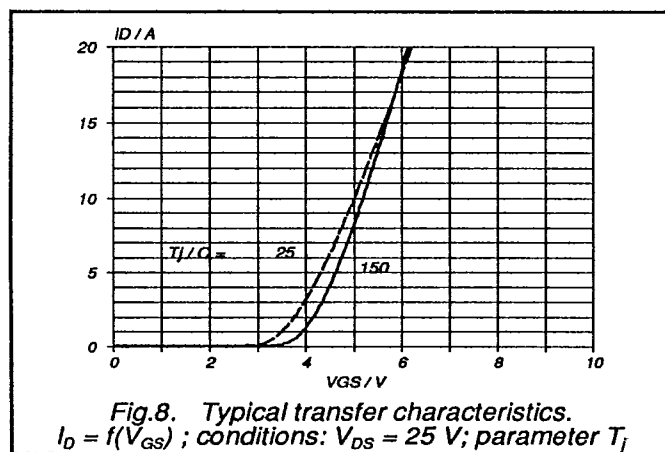
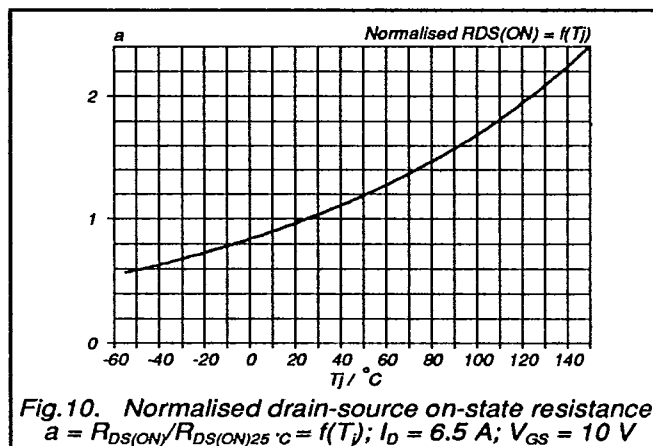
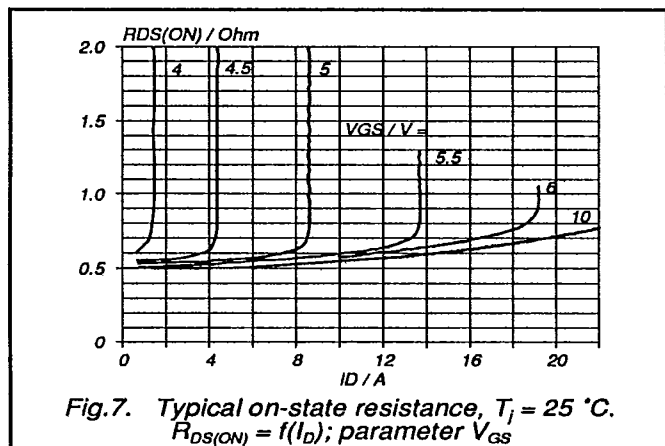
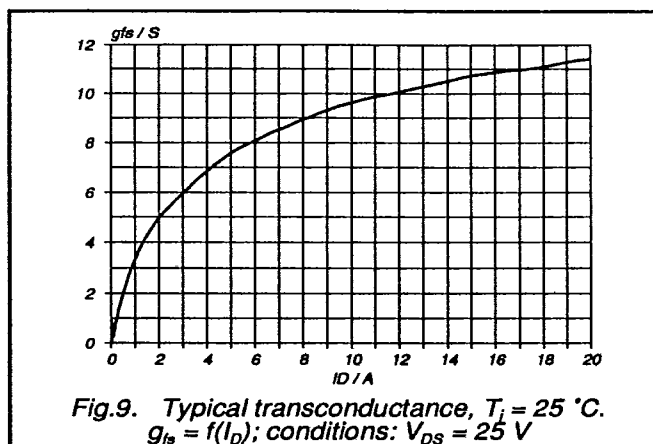
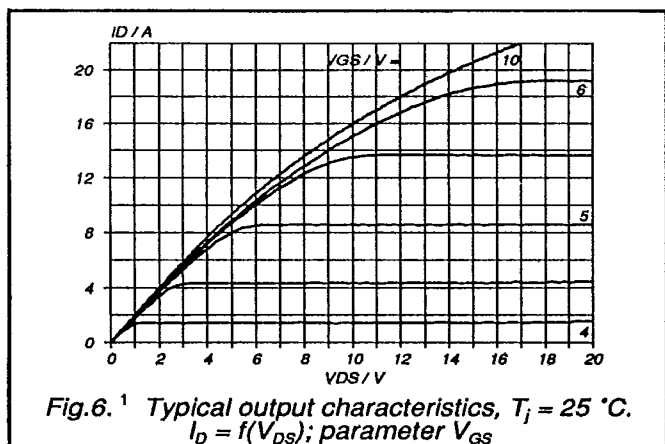
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
W_{OSS}	Drain-source non-repetitive unclamped inductive turn-off energy	$I_D = 10\text{ A}; V_{DD} \leq 250\text{ V}; V_{GS} = 10\text{ V}; R_{GS} = 50\ \Omega$	-	-	500	mJ



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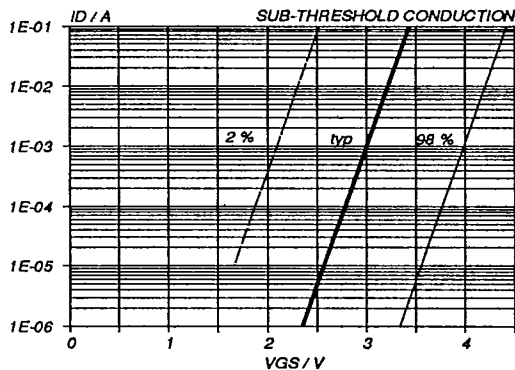


Fig. 12. Sub-threshold drain current.
 $I_D = f(V_{GS})$; conditions: $T_j = 25^\circ\text{C}$; $V_{DS} = V_{GS}$

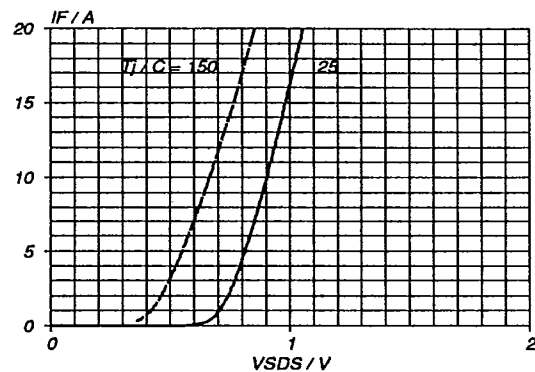


Fig. 15. Typical reverse diode current.
 $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0\text{ V}$; parameter T_j

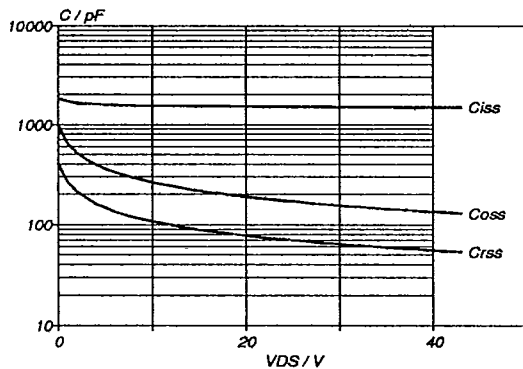


Fig. 13. Typical capacitances, C_{iss} , C_{oss} , C_{rss} .
 $C = f(V_{DS})$; conditions: $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$

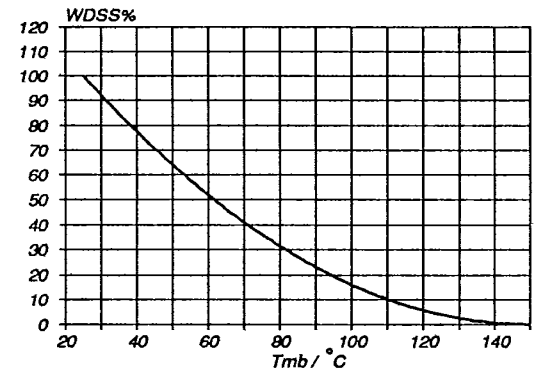


Fig. 16. Normalised avalanche energy rating.
 $W_{DSS}\% = f(T_{mb})$; conditions: $I_D = 10\text{ A}$

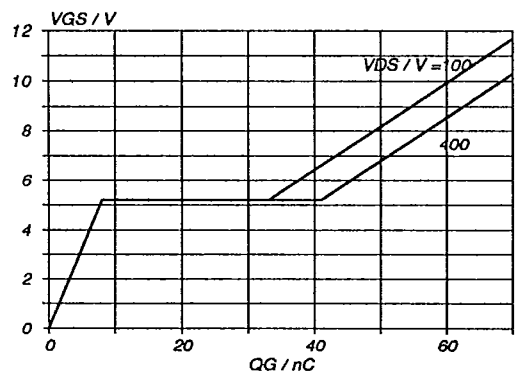


Fig. 14. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; conditions: $I_D = 10\text{ A}$; parameter V_{DS}

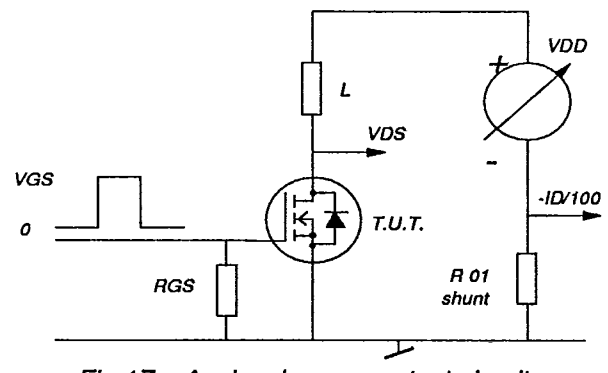


Fig. 17. Avalanche energy test circuit.
 $W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS} / (BV_{DSS} - V_{DD})$